

Isc N-Channel MOSFET Transistor

SPP15N60C3

• FEATURES

- Ultra low effective capacitances
- Low gate charge
- Improved transconductance
- Low gate drive power loss
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

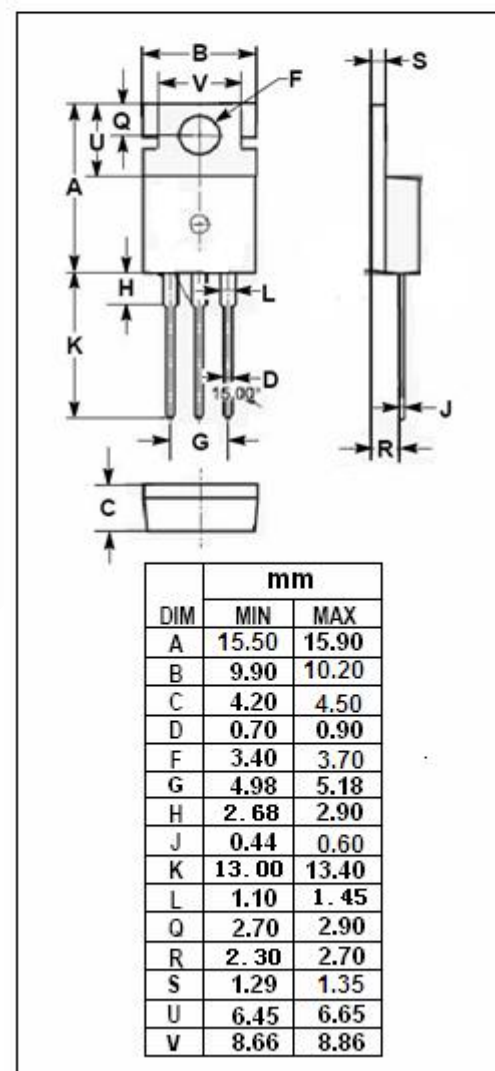
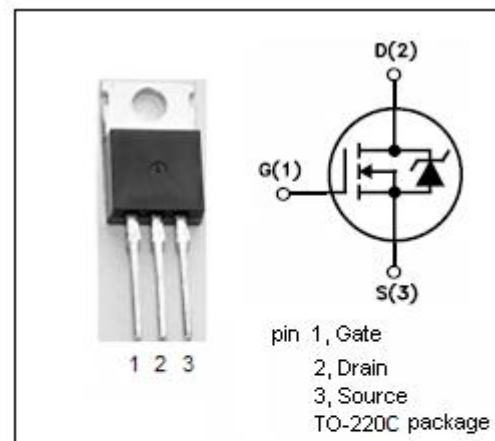
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	15 9.4	A
I_{DM}	Drain Current-Single Pulsed	45	A
P_D	Total Dissipation	156	W
T_j	Operating Junction Temperature	-55~175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~175	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.8	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^{\circ}\text{C/W}$





INCHANGE Semiconductor

Isc N-Channel MOSFET Transistor**SPP15N60C3****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =±30V; I _D =0.675mA	2.1		3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =9.4A		250	280	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V; T _J =25°C T _J =125°C			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =15A, V _{GS} = 0 V			1.2	V